

Search History

=> d 114 1-8 abs,bib

STN(HEATBUS, INSPEC, JAPPO, USPATFULL)
4/11/65

L14 ANSWER 1 OF 8 USPATFULL on STN

AB A process for preparing p-n or n-p junctions having a p-type oxide film is disclosed. In one embodiment, a p-type zinc oxide film has a net acceptor concentration of at least about 10.sup.15 acceptors/cm.sup.3.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2004:124122 USPATFULL

TI Process for preparing p-n junctions having a p-type ZnO film

IN White, Henry W., Columbia, MO, UNITED STATES
Zhu, Shen, Huntsville, AL, UNITED STATES

Ryu, Yungryel, Columbia, MO, UNITED STATES

PA The Curators of the University of Missouri (U.S. corporation)

PI US 2004094085 A1 20040520

AI US 2003-615102 A1 20030708 (10)

RLI Continuation of Ser. No. US 2001-2790, filed on 15 Nov 2001, GRANTED, Pat. No. US 6610141 Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, GRANTED, Pat. No. US 6342313 Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999, GRANTED, Pat. No. US 6410162 Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, GRANTED, Pat. No. US 6291085

DT Utility

FS APPLICATION

LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR, ST LOUIS, MO, 63102

CLMN Number of Claims: 77

ECL Exemplary Claim: 1

DRWN 9 Drawing Page(s)

LN.CNT 1049

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 2 OF 8 USPATFULL on STN

AB A p-type zinc oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, the p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type zinc oxide film has a net acceptor concentration of at least about 10.sup.15 acceptors/cm.sup.3, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.sup.2/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:152321 USPATFULL

TI Zinc oxide films containing p-type dopant and process for preparing same

IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States

Ryu, Yungryel, Columbia, MO, United States

PA The Curators of the University of Missouri, Columbia, MO, United States (U.S. corporation)

PI US 6410162 B1 20020625

AI US 1999-364809 19990730 (9)

RLI Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented, Pat. No. US 6291085

DT Utility

FS GRANTED

EXNAM Primary Examiner: Lam, Cathy

LREP Senniger, Powers, Leavitt & Roedel

CLMN Number of Claims: 25

ECL Exemplary Claim: 1

DRWN 10 Drawing Figure(s); 9 Drawing Page(s)

LN.CNT 804

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 3 OF 8 USPATFULL on STN

AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration** of at least about 10.¹⁵ acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:105800 USPATFULL

TI Zinc oxide films containing p-type dopant and process for preparing same

IN White, Henry W., Columbia, MO, UNITED STATES

Zhu, Shen, Huntsville, AL, UNITED STATES

Ryu, Yungryel, Columbia, MO, UNITED STATES

PA The Curators of the University of Missouri (U.S. corporation)

PI US 2002055003 A1 20020509

US 6610141 B2 20030826

AI US 2001-2790 A1 20011115 (10)

RLI Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, PATENTED
Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999,
PENDING Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug
1998, PATENTED

DT Utility

FS APPLICATION

LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR,
ST LOUIS, MO, 63102

CLMN Number of Claims: 81

ECL Exemplary Claim: 1

DRWN 9 Drawing Page(s)

LN.CNT 1060

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 4 OF 8 USPATFULL on STN

AB A p-type zinc oxide film

and a process for preparing the film is disclosed. In a preferred embodiment, the p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type zinc oxide film has a **net acceptor concentration** of at least about 10.¹⁵ acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:54520 USPATFULL

TI Zinc oxide films containing p-type dopant and process for preparing same

IN White, Henry W., Columbia, MO, UNITED STATES

Zhu, Shen, Huntsville, AL, UNITED STATES

Ryu, Yungryel, Columbia, MO, UNITED STATES

PI US 2002031680 A1 20020314

US 6475825 B2 20021105

AI US 2001-843205 A1 20010426 (9)

RLI Division of Ser. No. US 1998-128516, filed on 3 Aug 1998, GRANTED, Pat. No. US 6291085

DT Utility

FS APPLICATION

LREP SENNIGER POWERS LEAVITT AND ROEDEL, ONE METROPOLITAN SQUARE, 16TH FLOOR,
ST LOUIS, MO, 63102

CLMN Number of Claims: 50

ECL Exemplary Claim: 1

DRWN 4 Drawing Page(s)

LN.CNT 692

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 5 OF 8 USPATFULL on STN

AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration** of at least about 10.¹⁵ acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:19144 USPATFULL

TI Oxide films and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States

PA The Curators of the University of Missouri, Columbia, MO, United States
(U.S. corporation)

PI US 6342313 B1 20020129

AI US 1999-439529 19991112 (9)

RLI Continuation-in-part of Ser. No. US 1999-364809, filed on 30 Jul 1999
Continuation-in-part of Ser. No. US 1998-128516, filed on 3 Aug 1998,
now patented, Pat. No. US 6291085

DT Utility

FS GRANTED

EXNAM Primary Examiner: Jones, Deborah; Assistant Examiner: de la Pena, Jason

LREP Senniger, Powers, Leavitt & Roedel

CLMN Number of Claims: 13

ECL Exemplary Claim: 1

DRWN 10 Drawing Figure(s); 9 Drawing Page(s)

LN.CNT 807

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 6 OF 8 USPATFULL on STN

AB A p-type zinc oxide film and a process for preparing the film is disclosed. In a preferred embodiment, the p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type zinc oxide film has a **net acceptor concentration** of at least about 10.¹⁵ acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2001:157919 USPATFULL

TI Zinc oxide films containing p-type dopant and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States

PA The Curators of the University of Missouri, Columbia, MO, United States
(U.S. corporation)

PI US 6291085 B1 20010918

AI US 1998-128516 19980803 (9)

DT Utility

FS GRANTED

EXNAM Primary Examiner: Lorin, Francis J.

LREP Senniger, Powers, Leavitt & Roedel

CLMN Number of Claims: 30

ECL Exemplary Claim: 1

DRWN 5 Drawing Figure(s); 4 Drawing Page(s)

LN.CNT 608

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 7 OF 8 USPAT2 on STN

AB A p-type oxide film and a process for preparing the film and p-n or n-p junctions is disclosed. In a preferred embodiment, a p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type oxide film has a **net acceptor concentration of** at least about 10.5×10^{15} acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:105800 USPAT2

TI Zinc oxide films containing p-type dopant and process for preparing same
IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States

PA The Curators of the University of Missouri, Columbia, MO, United States
(U.S. corporation)

PI US 6610141 B2 20030826

AI US 2001-2790 20011115 (10)

RLI Division of Ser. No. US 1999-439529, filed on 12 Nov 1999, now patented,
Pat. No. US 6342313 Continuation-in-part of Ser. No. US 1999-364809,
filed on 30 Jul 1999 Continuation-in-part of Ser. No. US 1998-128516,
filed on 3 Aug 1998, now patented, Pat. No. US 6291085

DT Utility

FS GRANTED

EXNAM Primary Examiner: Hiteshew, Felisa

LREP Senniger, Powers, Leavitt & Roedel

CLMN Number of Claims: 40

ECL Exemplary Claim: 1

DRWN 10 Drawing Figure(s); 9 Drawing Page(s)

LN.CNT 976

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

L14 ANSWER 8 OF 8 USPAT2 on STN

AB A p-type zinc oxide film and a process for preparing the film is disclosed. In a preferred embodiment, the p-type zinc oxide film contains arsenic and is grown on a gallium arsenide substrate. The p-type zinc oxide film has a **net acceptor concentration of** at least about 10.5×10^{15} acceptors/cm.³, a resistivity of no greater than about 1 ohm-cm, and a Hall mobility of between about 0.1 and about 50 cm.²/Vs.

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

AN 2002:54520 USPAT2

TI Process for preparing zinc oxide films containing p-type dopant

IN White, Henry W., Columbia, MO, United States
Zhu, Shen, Huntsville, AL, United States
Ryu, Yungryel, Columbia, MO, United States

PA The Curators of the University of Missouri, Columbia, MO, United States
(U.S. corporation)

PI US 6475825 B2 20021105

AI US 2001-843205 20010426 (9)

RLI Division of Ser. No. US 1998-128516, filed on 3 Aug 1998, now patented,
Pat. No. US 6291085

DT Utility

FS GRANTED

EXNAM Primary Examiner: Sherry, Michael; Assistant Examiner: Pert, Evan

LREP Senniger, Powers, Leavitt & Roedel

CLMN Number of Claims: 24

ECL Exemplary Claim: 1

DRWN 5 Drawing Figure(s); 4 Drawing Page(s)

LN.CNT 660

CAS INDEXING IS AVAILABLE FOR THIS PATENT.

=> d his

(FILE 'HCAPLUS, INSPEC, JAPIO, USPATFULL, USPAT2' ENTERED AT 06:07:43 ON
11 APR 2005)

DELETE HIS

L1 19321 S (ZNO OR ZINC(W)OXIDE) (8A) (FILM#)
L2 248 S (NET(W)ACCEPTOR#) (8A) (CONCENTRATION#)
L3 146133 S (CLEAN? OR ETCH?) (6A) (SUBSTRATE#)
L4 8512 S (ADJUST? OR MANIPULAT? OR CHANG? OR ALTER?) (8A) (TEMPERATURE(6
L5 190433 S (PULS? (6A)LASER)
L6 315 S (P(W)TYPE) (8A) (ZNO(4A)FILM# OR ZINC(W)OXIDE(4A)FILM#)
L7 41 S (PELLET#) (8A) (PRESS? (6A)ZNO OR PRESS(6A)ZINC(W)OXIDE)
L8 1321353 S (POWDER#)
L9 10 S L1 AND L2
L12 8 S L1 AND L2 AND L3 AND L4 AND L5 AND L6
L13 8 S L7 AND L12
L14 8 S L1 AND L2 AND L3 AND L4 AND L5 AND L6 AND L7 AND L8

=>

Day : Monday
Date: 4/11/2005

Time: 11:12:56

 PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = WHITE

First Name = HENRY W.

Application#	Patent#	Status	Date Filed	Title	Inventor Name
09364809	6410162	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	WHITE, HENRY W.
09439529	6342313	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	WHITE, HENRY W.

Inventor Search Completed: No Records to Display.

Search Another: Inventor

Last Name	First Name
<input type="text" value="White"/>	<input type="text" value="Henry W."/>
<input type="button" value="Search"/>	

To go back use Back button on your browser toolbar.

Back to [PALM](#) | [ASSIGNMENT](#) | [OASIS](#) | Home page

Day : Monday
Date: 4/11/2005

Time: 11:13:26

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = ZHU

First Name = SHEN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09128516</u>	<u>6291085</u>	150	08/03/1998	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
<u>09364809</u>	<u>6410162</u>	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
<u>09439529</u>	<u>6342313</u>	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	ZHU, SHEN
<u>09843205</u>	<u>6475825</u>	150	04/26/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
<u>10002790</u>	<u>6610141</u>	150	11/15/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	ZHU, SHEN
<u>10615102</u>	Not Issued	030	07/08/2003	PROCESS FOR PREPARING P-N JUNCTIONS HAVING A P-TYPE ZNO FILM	ZHU, SHEN
<u>09075555</u>	<u>6022261</u>	150	05/08/1998	VERTICALLY SINKABLE TOY SHIP MODEL	ZHU, SHENG BO
<u>07436885</u>	Not Issued	161	11/14/1989	METHOD FOR PRODUCING A NON-MAXWELLIAN KINETIC ENERGY DISTRIBUTION IN A COLLECTION OF LOW-MASS PARTICLES	ZHU, SHENG- BAI
<u>11052725</u>	Not Issued	020	02/07/2005	SOLID-STATE LASERS EMPLOYING INCOHERENT MONOCHROMATIC PUMP	ZHU, SHENG- HAI
<u>07455070</u>	<u>5126971</u>	150	12/22/1989	THIN FILM MAGNETIC CORE MEMORY AND METHOD OF	ZHU, SHENGBO

MAKING SAME					
<u>07463567</u>	5072324	150	01/11/1990	THIN FILM TRANSDUCER/TRANSFORMER ASSEMBLY	ZHU, SHENGBO
<u>07772981</u>	Not Issued	166	10/07/1991	MINIATURE TRANSDUCER/SIGNAL BOOSTER ASSEMBLY	ZHU, SHENGBO
<u>07781713</u>	Not Issued	166	10/22/1991	THIN FILM TRANSDUCER WITH COIL GUARD SEGMENT	ZHU, SHENGBO
<u>07847765</u>	Not Issued	161	03/05/1992	MAGNETIC SLIDER WITH IMPROVED SUBSTRATE MATERIAL	ZHU, SHENGBO
<u>07847770</u>	5305168	150	03/05/1992	THIN FILM TRANSDUCER SUSPENION ASSEMBLY WITH FLEXURE-MOUNTED BOOSTER ELEMENT	ZHU, SHENGBO
<u>07878701</u>	5831800	250	05/05/1992	MINIATURE TRANSFORMER FOR READ/WRITE TRANSDUCER	ZHU, SHENGBO
<u>07879405</u>	Not Issued	166	05/05/1992	MINIATURE THIN FILM INDUCTIVE DEVICE WITH ADDITIONAL MAGNETIC MATERIAL IN THE CONTACT REGION BETWEEN POLE PIECES	ZHU, SHENGBO
<u>07998751</u>	Not Issued	161	12/29/1992	MINIATURE TRANSDUCER/TRANSFORMER ASSEMBLY	ZHU, SHENGBO
<u>08071787</u>	Not Issued	161	06/04/1993	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
<u>08193667</u>	Not Issued	161	02/08/1994	THIN FILM TRANSDUCER WITH COIL GUARD SEGMENT	ZHU, SHENGBO
<u>08193668</u>	Not Issued	161	02/08/1994	MINIATURE THIN FILM INDUCTIVE DEVICE WITH ADDITIONAL MAGNETIC MATERIALIN THE CONTACT REGION BETWEEN POLE PIECES	ZHU, SHENGBO
<u>08322030</u>	Not Issued	166	10/12/1994	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
<u>08651438</u>	Not Issued	161	05/22/1996	THIN FILM TRANSDUCER WITH REDUCED FLYING HEIGHT	ZHU, SHENGBO
<u>08685290</u>	Not Issued	161	07/23/1996	ELECTRIC FAN COOLING SYSTEM WITH TEMPERATURE SENSED SPEED CONTROL	ZHU, SHENGBO

<u>08886271</u>	Not Issued	169	07/01/1997	HELICAL PLANAR HEAD	ZHU, SHENGBO
<u>09115728</u>	6360953	150	07/15/1998	SECURE PRINT SENSING SMART CARD WITH ON-THE-FLY-OPERATION	ZHU, SHENGBO
<u>09131798</u>	Not Issued	161	08/10/1998	VOICE RESPONSIVE PAPER SHREDDER WITH DECORATIVE CASING	ZHU, SHENGBO
<u>09144391</u>	5977875	150	08/31/1998	COLLECTIVE OBJECTS MANAGEMENT SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
<u>09161175</u>	Not Issued	161	09/25/1998	INVENTORY CONTROL SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
<u>09506509</u>	6819222	150	02/17/2000	INVENTORY CONTROL SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
<u>09506652</u>	6791398	150	02/17/2000	DATA TOKEN WITH POWER SAVING SWITCH	ZHU, SHENGBO
<u>09541672</u>	6567010	150	03/31/2000	TRAFFIC SIGNAL HEAD WITH MULTIPLE LED ILLUMINATION SOURCES	ZHU, SHENGBO
<u>09565992</u>	6348864	150	05/06/2000	ORGANIZER MANAGEMENT SYSTEM USING R.F. IDENTIFICATION	ZHU, SHENGBO
<u>09751198</u>	6664895	150	01/02/2001	R.F. SUPPRESSION TECHNIQUE FOR COLLECTIVE OBJECTS MANAGEMENT SYSTEM USING R.F. OBJECT IDENTIFICATION	ZHU, SHENGBO
<u>10900485</u>	Not Issued	030	07/28/2004	MULTI-PHASE A.C. VEHICLE MOTOR	ZHU, SHENGBO
<u>10804811</u>	Not Issued	030	03/19/2004	IDENTIFYING EARLY ADOPTERS AND ITEMS ADOPTED BY THEM	ZHU, SHENGHUO
<u>09235190</u>	6297507	150	01/22/1999	SEALED TUBE NEUTRON GENERATOR INCORPORATING AN INTERNAL ASSOCIATED-ALP	ZHU, SHENGJIANG

Inventor Search Completed: No Records to Display.

Search Another: Inventor	Last Name	First Name
	<input type="text" value="Zhu"/>	<input type="text" value="Shen"/>
	<input type="button" value="Search"/>	

To go back use Back button on your browser toolbar.

Day : Monday
Date: 4/11/2005

Time: 11:13:47

PALM INTRANET**Inventor Name Search Result**

Your Search was:

Last Name = RYU

First Name = YUNGRYEL

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09128516</u>	<u>6291085</u>	150	08/03/1998	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
<u>09364809</u>	<u>6410162</u>	150	07/30/1999	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
<u>09439529</u>	<u>6342313</u>	150	11/12/1999	OXIDE FILMS AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
<u>09843205</u>	<u>6475825</u>	150	04/26/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
<u>10002790</u>	<u>6610141</u>	150	11/15/2001	ZINC OXIDE FILMS CONTAINING P-TYPE DOPANT AND PROCESS FOR PREPARING SAME	RYU, YUNGRYEL
<u>10615102</u>	Not Issued	030	07/08/2003	PROCESS FOR PREPARING P- N JUNCTIONS HAVING A P- TYPE ZNO FILM	RYU, YUNGRYEL
<u>60406500</u>	Not Issued	159	08/28/2002	HYBRID BEAM DEPOSITION SYSTEM AND METHOD FOR FABRICATING METAL OXIDE ZNO FILMS, P-TYPE ZNO FILMS, AND ZNO - BASED II-VI GROUP COMPOUND SEMICONDUCTOR DEVICES	RYU, YUNGRYEL
<u>60647177</u>	Not Issued	020	01/25/2005	HIGH-PERFORMANCE FET DEVICES AND METHODS	RYU, YUNGRYEL

Inventor Search Completed: No Records to Display.

6,610,141
6,342,313
6,410,1620
6,291,085

Search
117/8, 54
438/642, 697, 699
438/46, 104

10/615, 102

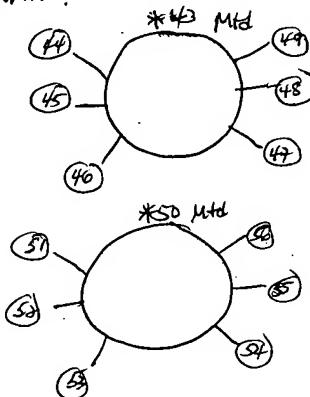
Examiner's Notes

S (ZnO or zinc(II) oxide) (8a) (f) (M#)
S (net (II) acceptor) (8a) (concentration)
S (clear?) (8a) (substrate)
S (adjusts or manipulates or changes or alters?) (8a) (temperature (and substrate))
S (pulsed) (8a) (rate)
S (p (II) type) (8a) (ZnO (II) filter or zinc(II) oxide (filter))
S (pelletted) (8a) (press? (8a) ZnO or press? (8a) zinc(II) oxide)
S (powder)

112 P2 Reg:

Claim 43, line 2, "... net acceptor...".

Claim 50, line 3, "... net acceptor...".



ODP

U.S. Pat. No. 6,610,141 B2 (White, et al.) claims 1-39,
U.S. Pat. No. 6,475,825 B2 (White, et al.) claims 1-29,
U.S. Pat. No. 6,410,162 B2 (White, et al.) claims 1-25,
U.S. Pat. No. 6,291,085 B2 (White, et al.) claims 1-30
U.S. Pat. No.

8.08 1) $\sqrt{S^1-29 \& 72-77}$ are
2) [A ZnO film + an oxide film
Group I 3) $\sqrt{432}$

Prod 4) $\sqrt{328.2}$

5) $\sqrt{S^30-56} \sqrt{b^1-71}$

Group II 6) A process for growing a p-type ZnO film containing As on a Ge substrate

Mtd 7)

8)

8.09 1) $\sqrt{S^57-58}$

Group III 2) A process for cleaning a substrate in a chamber

Mtd 3) $\sqrt{432}$

4) $\sqrt{6897}$

8. ~~RF 42-77~~

Group IV